

# R65C00 CMOS Microcomputer System DATA SHEET

# **R65C00 MICROPROCESSORS (CPU)**

# DESCRIPTION

The 8-bit R65C00 microcomputer system is produced with CMOS Silicon Gate technology. Advanced system architecture enhances its performance speeds; a family of software-compatible microprocessor (CPU) devices (described below) enhances system cost-effectiveness. Rockwell also provides memory and microcomputer systems, as well as low-cost design aids and documentation.

# R65C00 MICROPROCESSOR (CPU) CONCEPT

Three CPU devices are available. All are software-compatible and provide addressable memory, interrupt input, and on-chip clock oscillators and drivers options. All are buscompatible with the NMOS R6500 family devices.

The family includes two microprocessors with on-board clock oscillators and drivers and one microprocessor driven by external clocks. The on-chip clock versions are aimed at high performance, low cost applications where single phase inputs, crystal or RC inputs provide the time base. The slave processor version is geared for multiprocessor system applications where maximum timing control is mandatory. All R65C00 microprocessors are available in a variety of packaging (ceramic and plastic), operating frequency (2 MHz, 3 MHz and 4 MHz), and temperature (commercial and industrial) versions.

# MEMBERS OF THE R65C00 MICROPROCESSOR (CPU) FAMILY

Microprocessors with Internal Clock Generator:

Model

Addressable Memory

R65C02

64K Bytes

R65C102

64K Bytes

Microprocessors with External Clock Input:

Model

Addressable Memory

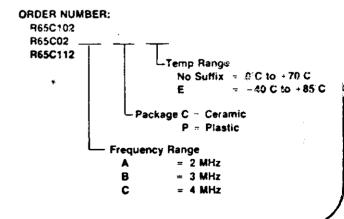
R65C112

64K Bytes

### **FEATURES**

- CMOS silicon gate technology
- Low Power (4MA MHz)
- Downward software compatible with R6502
  - —Twelve additional instructions
  - -Two new addressing modes
- Single 5V ±20% power supply
- Eight bit parallel processing
- · Decimal and binary arithmetic
- True indexing capability
- Programmable stack pointer
- Interrupt capability
- Non-maskable interrupt
- Use with any type of speed memory.
- Eight-bit Bidirectional Data Bus
- o Addressable memory range of up to 64K bytes
- "Ready" input
- Direct Memory Access capability
- Memory Lock Output
- o 2MHz, 3MHz, and 4MHz versions
- · Choice of external or on-chip clocks
- On-the-chip clock options
  - -External single clock input
  - --- Direct Crystal Input (÷ 4)
- Commercial and industrial temperature versions
- Pipeline architecture
- Slave Processor Version (R65C112)

#### ORDERING INFORMATION



**PRELIMINARY** 

Document No. 29000D91 Order No. D91 Rev. 1 November 1982

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# SIGNAL DESCRIPTION

Clocks  $(\phi_0, \phi_1, \phi_2, \phi_4)$ 

The R65C112 requires an external  $\phi_2$  clock.

The R65C02 requires an external φ<sub>0</sub> clock.

The R65C102 clocks may be generated externally or internally with a crystal across XTLI and XTLO.

φ<sub>0</sub>--TTL input clock to the R65C02

 $\phi_4$ —Quadrature output clock from the R65C102. The address is valid at the rising edge of  $\phi_4$ .

When the input clock is stopped the CPU is in the standby mode.

## Address Bus (A0-A15)

These outputs are TTL compatible and capable of driving one standard TTL load and 130 pF.

#### Pata Bus (D0-D7)

transferring data to and from the device and peripherals. The outputs are tri-state buffers capable of driving one standard TTL load and 130 pF.

## Ready (RDY)

This input signal allows the user to halt or single step the microprocessor on all cycles. A negative transition to the low state during or coincident with phase one  $(\phi_3)$  will halt the microprocessor with the output address lines reflecting the current address being accessed. During a Write cycle the data bus will reflect the current data being written.

While RDY is low the CPU is in a low power mode.

#### Bus Enable (BE)

The BE input allows an external device to tri-state the address, data, and R/W lines by taking this line to a logical zero state.

## Interrupt Request (IRQ)

This TTL level input requests that an interrupt sequence begin within the microprocessor. The microprocessor will complete the instruction being executed before recognizing the request. At that time, the interrupt mask bit in the Status Code Register will be examined. If the interrupt mask flag is not set, the microprocessor will begin an interrupt sequence.

• Program Counter and Processor Status Register are used in the stack. The microprocessor will then set the interrupt mask flag high so that no further interrupts may occur. At the end of this cycle, the program counter low will be loaded from address FFFE and program counter high from location FFFF, thus transferring program control to the

mory vector located at these addresses. The RDY signal must be in the high state for any interrupt to be recognized. An external pull-up resistor should be used for proper wire-OR operation.

## Non-Maskable Interrupt (NMI)

A negative going edge on this input requests that a non-maskable interrupt sequence be generated within the microprocessor.

NMI is an unconditional interrupt. Following completion of the current instruction, the sequence of operations defined for IRQ will be performed, regardless of the state of the interrupt mask flag. The vector address loaded into the program counter, low and high, are locations FFFA and FFFB respectively, thereby transferring program control to the memory vector located at these addresses. The instructions loaded at these locations cause the microprocessor to branch to a non-maskable interrupt routine in memory.

NMI requires an external resistor to V<sub>cc</sub> for proper wire-OR operations.

Inputs  $\overline{\text{IRQ}}$  and  $\overline{\text{NMI}}$  are hardware interrupts lines sampled during  $\phi_2$  (phase 2). They begin the appropriate interrupt routine on the  $\phi_1$  (phase 1) following the completion of the current instruction.

## Set Overflow Flag (S.O.)

A negative going edge on this input sets the overflow bit in the Status Code Register. This signal is sampled on the trailing edge of  $\phi_1$  and must be externally synchronized.

#### SYNC

This output line identifies those cycles in which the microprocessor is doing an OP CODE fetch. The SYNC line goes high during  $\phi_1$  of an OP CODE fetch and stays high for the remainder of that cycle. If the RDY line is pulled low during the  $\phi_1$  clock pulse in which SYNC went high, the processor will stop in its current state and will remain there until the RDY line goes high. In this manner the SYNC signal can be used to control RDY to cause single instruction execution.

#### Reset

This input resets or starts the microprocessor from a power down condition. During the time that this line is held low, writing to or from the microprocessor is inhibited. When a positive edge is detected on the input, the microprocessor will immediately begin the reset sequence.

After a system initialization time of six clock cycles, the mask interrupt flag will be set and the microprocessor will load the program counter from the memory vector locations FFFC and FFFD. This is the start location for program control.

This fine is a Schmitt trigger input which facilitates the use of an RC network as a power on reset circuit.

# Memory Lock (ML)

This output may be used by external bus arbitration circuitry to avoid the interruption of read-modify-write instructions. These instructions are ASL, DEC, INC, LSR, RMB, ROR, SMB, TRB, and TSB.

## ADDRESSING MODES

ACCUMULATOR ADDRESSING-This form of addressing is represented with a one byte instruction, implying an operation on the accumulator.

IMMEDIATE ADDRESSING-In immediate addressing, the second byte of the instruction contains the operand, with no further memory addressing required.

ABSOLUTE ADDRESSING-In absolute addressing, the second byte of the instruction specifies the eight low order bits of the effective address while the third byte specifies the eight high order bits. Thus, the absolute addressing mode allows access to the entire 64K bytes of addressable memory.

ZERO PAGE ADDRESSING-The zero page instructions allow for shorter code and execution times by fetching only the second byte of the instruction and assuming a zero high address byte. Careful use of the zero page can result in significant increase in code efficiency.

INDEXED ZERO PAGE ADDRESSING-(X, Y indexing)-This form of addressing is used with the index register and is referred to as "Zero Page, X" or "Zero Page, Y". The effective address is calculated by adding the second byte to the contents of the index register. Since this is a form of "Zero Page" addressing, the content of the second byte references a location in page zero. Additionally, due to the "Zero Page" addressing nature of this mode, no carry is added to the high order eight bits of memory and crossing of page boundaries does not occur.

INDEXED ABSOLUTE ADDRESSING-(X, Y indexing)-This form of addressing is used in conjunction with X and Y index register and is referred to as "Absolute, X" and "Absolute, Y". The effective address is formed by adding the contents of X or Y to the address contained in the second and third bytes of the instruction. This mode allows the index register to contain the index or count value and the instruction to contain the base address. This type of indexing allows any location referencing and the index to modify multiple fields, resulting in reduced coding and execution time.

INDEXED ABSOLUTE INDIRECT—(new addressing mode-JMP (IND), X)—The contents of the second and third instruction bytes are added to the X-register. The sixteen-bit result is a memory address containing the effective address.

IMPLIED ADDRESSING-In the implied addressing mode, the address containing the operand is implicitly stated in the '. operation code of the instruction.

RELATIVE ADDRESSING-Relative addressing is used only with branch instructions and establishes a destination for the conditional branch.

The second byte of the instruction becomes the operand which is an "Offset" added to the contents of the lower eight bits of the program counter when the counter is set at the next instruction. The range of the offset is -128 to +127 bytes from the next instruction.

INDEXED INDIRECT ADDRESSING-In indexed indirect addressing (referred to as (Indirect, X)), the second byte of the instruction is added to the contents of the X index register, discarding the carry. The result of this addition points to a memory location on page zero whose contents are the low order eight bits of the effective address. The next memory location in page zero contains the high order eight bits of the effective address. Both memory locations specifying the high and low order bytes of the effective address must be in page zero.

INDIRECT INDEXED ADDRESSING-In indirect indexed addressing (referred to as (Indirect), Y), the second byte of the instruction points to a memory location in page zero. The contents of this memory location are added to the contents of the Y index register, the result being the low order eight bits of the effective address. The carry from this addition is added to the contents of the next page zero memory location, the result being the high order eight bits of the effective address.

ABSOLUTE INDIRECT—The second byte of the instruction contains the low order eight bits of a memory location. The high order eight bits of that memory location are contained in the third byte of the instruction. The contents of the fully specified memory location are the low order byte of the effective address. The next memory location contains the high order byte of the effective address which is loaded into the sixteen bits of the program counter. (JMP (IND) only)

INDIRECT--(new addressing mode)-The second byte of the instruction contains a zero page address serving as the indirect pointer.

# INSTRUCTION SET ALPHABETIC SEQUENCE

Mne	monic	Function	Mner	nonic	Function
(2)	ADC	Add Memory to Accumulator with Carry		NOP	No Operation
(2)	AND	"AND" Memory with Accumulator	1	1	·
• •	ASL	Shift Left One Bit (Memory or Accumulator)	(2)	ORA	"OR" Memory with Accumlator
(1)	BBR	Branch on Bit Reset		РНА	Push Accumulator on Stack
(1)	BBS	Branch on Bit Set		PHP	Push Processor Status on Stack
` ′	всс	Branch on Carry Clear	(1)	PHX	Push X Register on Stack
	BCS	Branch on Carry Set	(1)	PHY	Push Y Register on Stack
	BEQ	Branch on Result Zero		PLA	Pull Accumulator from Stack
(2)	BIT	Test Bits in Memory with Accumulator		PLP	Pull Processor Status from Stack
` '	ВМІ	Branch on Result Minus	(1)	PLX	Pull X Register from Stack
	BNE	Branch on Result not Zero	(1)	PLY	Pull Y Register from Stack
	8PL	Branch on Result Plus	`´		_
(1)	BRA	Branch Always	(1)	RMB	Reset Memory Bit
• • •	BRK	Force Break	''	ROL	Rotate One Bit Left (Memory or Accumulator)
	BVC	Branch on Overflow Clear	i	ROR	Rotate One Bit Right (Memory or Accumulator)
	BVS	Branch on Overflow Set		RT≀	Return from Interrupt
				RTS	Return from Subroutine
	CLC	Clear Carry Flag	1		
	CLD	Clear Decimal Mode	1	SBC	Subtract Memory from Accumulator with Borrow
	CLI	Clear Interrupt Disable Bit		SEC	Set Carry Flag
	CLV	Clear Overflow Flag	ļ	SED	Set Decimal Mode
(2)	CMP	Compare Memory and Accumulator	1	ŞEI	Set Interrupt Disable Status
1-,	CPX	Compare Memory and Index X	(1)	SMB	Set Memory Bit
	CPY	Compare Memory and Index Y	(2)	STA	Store Accumulator in Memory
			]	STX	Store Index X in Memory
(2)	DEC	Decrement Memory by One	1	STY	Store Index Y in Memory
	DEX	Decrement Index X by One	(1)	STZ	Store Zero
	DEY	Decrement Index Y by One	1		
				TAX	Transfer Accumulator to Index X
(2)	EOR	"Exclusive-OR" Memory with Accumulator	1	TAY	Transfer Accumulator to Index Y
			(1)	TRB	Test and Reset Bits
(2)	INC	Increment Memory by One	(1)	TSB	Test and Set Bits
	INX	Increment Index X by One	}	TSX	Transfer Stack Pointer to Index X
	INY	Increment Index Y by One		TXA	Transfer Index X to Accumulator
	1			TXS	Transfer Index X to Stack Register
(2)	JMP	Jump to New Location	İ	TYA	Transfer Index Y to Accumulator
	JSR	Jump to New Location Saving Return Address			
(2)	LDA	Load Accumulator with Memory			
	LDX	Load Index X with Memory			
	LDY	Load Index Y with Memory	1		
	LSR	Shift One Bit Right (Memory or Accumulator)	!		

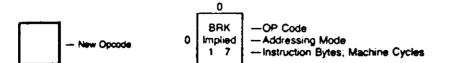
## NOTES:

(1) New Instruction

(2) Previous Instruction with additional addressing mode(s)



	SD 0	1	2	3	4	5	6	7	8	9	A	8	С	0	E	F	_
O	BRK Implied 1 7	ORA (IND, X) 2 6			TSB ZP 2 5	ORA ZP 2 3	ASL ZP 2 5	7P 2 5	PHP Implied 1 3	ORA IMM 2 2	ASL Accum 1 2		TSB ABS 3 6	ORA ABS 3 4	ASL ABS 3 6	BBR0 ZP 3 5**	٥
1	BPL Relative	ORA (IND), Y 2 5*	ORA (IND) 2 5		TRB ZP 2 5	ORA ZP, X 2 4	ASL ZP. X 2 6	RM81 ZP 2 5	CLC Implied 1 2	ORA ABS, Y	INC Accum 1 2		TRB ABS 3 6	ORA ABS. X 3 4'	ASL ABS, X 3 7	88A1 2P 3 5**	,
2	JSR Absolute	AND (IND, X)	. 3		BIT ZP	AND ZP	ROL ZP	RMB2 ZP	PLP Implied	AND	ROL Accum		BIT ABS	AND ABS	ROL ABS	BBR2 ZP	2
3	3 6 BMI Relative	2 6 AND (IND), Y	AND (IND)		BIT ZP, X	2 3 AND ZP, X	2 5 ROL ZP X	2 5 RMB3 ZP	SEC Implied	AND ABS, Y	DEC Accum		BIT ABS, X	AND ABS, X	3 6 FIOL ABS, X	BBR3 ZP	3
4	2 2" ATI Implied	EOR	2 5		2 4	2 4 EOR ZP	2 6 LSR ZP	2 5 RMB4 ZP	1 2 PHA Implied	EOR	1 2 LSR Accum		JMP ABS	3 4° EOR ABS	LSR ABS	3 5** BBR4 ZP	
5	1 6 BVC	2 6 EOR (IND), Y	EOR		<u> </u>	2 3 EOR ZP, X	2 5 LSR ZP X	2 5 RMB5	1 3	2 2 EOR ABS, Y	1 2 PHY	<u>: :</u>	3 3	3 4 EOR ABS, X	3 6 LSR ABS, X	3 5" 88R5 <i>Z</i> P	5
3	Relative 2 2" RTS	2 5°	(IND) 2 5		STZ	2 4 ADC	2 6 ROR	2 5 RMB6	implied 1 2 PLA	3 4°	Implied 1 2 ROR		JMP	3 4°	3 7 ROR	3 5°° BBR6	
6	Implied 1 6 BVS	(IND, X) 2 6† ADC	ADC		ZP 2 3 STZ	ZP 2 3† ADC	ZP 2 5 ROR	ZP 2 5 RMB7	Implied 1 4 SEI	IMM 2 2†	Accum 1 2 PLY		Indirect 3 5 JMP	ABS 3 4† ADC	ABS 3 6 BOR	3 5" BBR7	6
7	Relative 2 2"	(IND), Y 2 5°†	(IND) 2 5t		ZP, X 2 4	ZP, X 2 4†	ZP. X 2 6	ZP 2 5	Implied 1 2	ABS, Y 3 4°†	Implied 1 2		(IND) X 3 6	ABS. X 3 4'1	ABS, X 3 7	ZP 3 5"	7
8	BRA Relative 2 3	STA (IND, X) 2 6			STY ZP 2 3	STA ZP 2 3	STX ZP 2 3	SMB0 ZP 2 5	DEY Implied 1 2	8IT IMM 2 2	TXA Implied 1 2		STY ABS 3 4	STA ABS 3 4	STX ABS 3 4	8850 ZP 3 5"	8
9	BCC Relative 2 2"	STA (IND), Y 2 6	STA (IND) 2 6		STY ZP, X 2 4	STA ZP. X 2 4	STX ZP. Y 2 4	SMB1 ZP 2 5	TYA Implied 1 2	STA ABS Y 3 5	TXS Implied 1 2	•	STZ ABS 3 4	STA ABS X 3 5	STZ ABS, X 3 5	88S1 ZP 3 5"	9
A	LDY IMM 2 2	LDA (IND, X) 2 6	LDX IMM 2 2		LDY ZP 2 3	LDA ZP 2 3	LDX ZP 2 3	SMB2 ZP 2 5	TAY Implied 1 2	LDA IMM 2 2	TAX Implied 1 2		LDY ABS 3 4	LDA ABS 3 4	LDX ABS 3 4	BBS2 ZP 3 5"	^
В	BCS Relative 2 2"	LDA (IND), Y 2 5*	LDA (IND) 2 5		LDY ZP, X 2 4	LDA ZP. X 2 4	LDX ZP Y 2 4	SMB3 ZP 2 5	CLV Implied 1 2	LDA ABS, Y 3 4°	TSX Implied 1 2		LDY ABS, X 3 4	LDA ABS, X 3 4	LDX ABS. Y 3 4*	BBS3 ZP 3 5"	В
С	CPY IMM 2 2	CMP (IND, X) 2 6			CPY ZP 2 3	CMP ZP 2 3	DEC ZP 2 5	SMB4 ZP 2 5	INY Implied 1 2	CMP IMM 2 2	DEX Implied		CPY ABS 3 4	CMP ABS 3 4	DEC ABS 3 6	BBS4 ZP 3 5"	С
D	BNE Relative 2 2"	CMP	CMP (IND) 2 5			CMP ZP, X 2 4	DEC ZP, X 2 6	SMB5 ZP 2 5	CLD Implied 1 2	CMP ABS, Y 3 4'	PHX			CMP ABS, X 3 4	DEC ABS, X 3 7	B8S5 ZP 3 5"	D
E	CPX IMM	SBC (IND, X)			CPX ZP	SBC ZP	INC ZP	SMB6 ZP	INX Implied	SBC	NOP Implied		CPX ABS	SBC ABS	INC ABS	BBS6 ZP	E
F	2 2 BEQ Relative	SBC (IND), Y	SBC (IND)		2 3	SBC ZP, X	2 5 INC ZP, X	2 5 SMB7 ZP	1 2 SED Implied	2 2† SBC ABS, Y	1 2 PLX Implied		3 4	SBC ABS, X	3 6 INC ABS, X	3 5" BBS7 ZP	F
ļ	2 2"	2 5'1	2 5†			2 41	2 6	2 5	1 2	3 4°t	1 2		<u> </u>	3 4"†	3 7	3 5"	•
	0	1	2	3	4	5	6	7	8	9	A	8	С	D	E	F	



<sup>†</sup>Add 1 to N if in decimal mode.

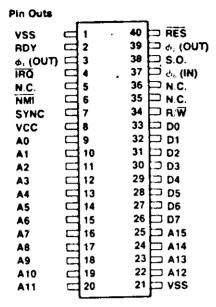
<sup>&</sup>quot;Add 1 to N if page boundary is crossed.

<sup>&</sup>quot;Add 1 to N if branch occurs to same page; Add 2 to N if branch occurs to different page.

# INSTRUCTION SUMMARY

# HARDWARE SPECIFICATIONS

## R65C02-40 Pin Package



#### **FEATURES**

- Pin Compatible with NMOS R6502
- 64K Addressable Bytes of Memory (A0-A15)
- IRQ Interrupt
- On-the-chip Clock
  - -TTL Level Single Phase Input
- SYNC Signal (can be used for single instruction execution)
- RDY Signal (can be used to halt or single cycle execution)
- Two Phase Output Clock for Timing of Support Chips
- NMI Interrupt

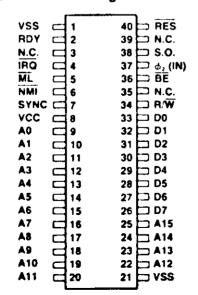
### R65C102-40 Pin Package

	_		_		
vss	႕	1	40	þ	RES
RDY		2	39	1	$\phi_{z}$ (OUT)
φ. (OUT)	◁	3	38	Þ	S.O.
ĪRŌ	ᄅ	4	37	$\vdash$	XTLI
ML	◁	5	36	Þ	BÉ
NMI	◁	6	35	₽	XTLO
SYNC	ㅁ	7	34	Þ	R/W
VCC	ᅥ	8	33	Þ	D0
AO	ᅥ	9	32	Þ	D1
A1	d	10	31	$\Box$	D2
A2		11	30	Þ	D3
A3	$\Box$	12	29	Þ	D4
A4		13	28	Þ	D5
A5		14	27	口	D6
A6	d	15	26	Þ	D7
A7		16	25	Ь	A15
AB	$\Box$	17	24	Ь	A14
A9	$\exists$	18	23	Ь	A13
A10	$\exists$	19	22	Ь	A12
A11	$\Box$	20	21	Ь	VSS
		i		ı	

## **FEATURES**

- φ<sub>4</sub> Quadrature Clock Output eases access time requirements
- 64K Addressable Bytes of Memory (A0-A15)
- IRQ Interrupt
- On-the-chip Clock
  - —TTL Level Single Phase Input
  - -RC Time Base Input
  - -Crystal Time Base Input (+ 4)
- SYNC Signal (can be used for signal instruction execution)
- RDY Signal (can be used to halt or single cycle execution)
- Two Phase Output Clock for Timing of Support Chips
- NMI Interrupt
- Direct Memory Access Capability
- Memory Lock Output
- Bus Enable Signal

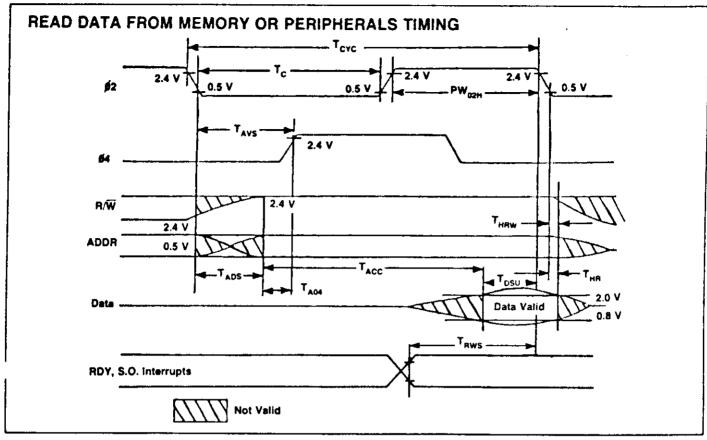
#### R65C112-40 Pin Package

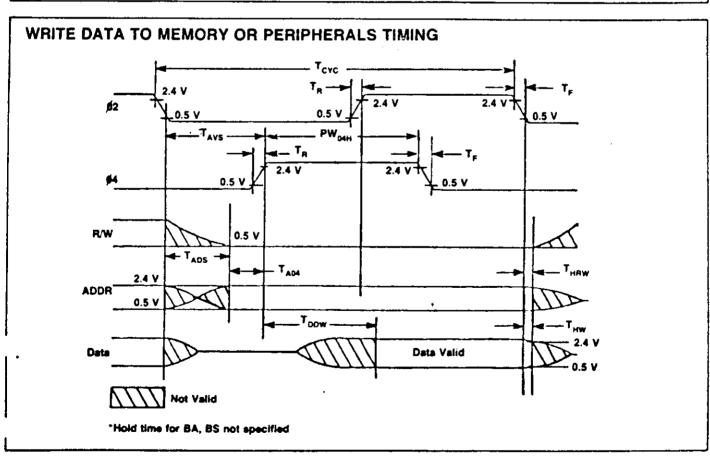


### **FEATURES**

- Slave Processor Version
- 64K Addressable Bytes of Memory (A0-A15)
- ÎÂQ Interrupt
- NMI interrupt
- RDY Signal
- 8 Bit Bidirectional Data Bus
- SYNC and RDY Signal
- Two phase clock input
- Bus Enable
- Direct Memory Access capability
- Memory Lock Output

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# A.C. Electrical Timing Characteristics

		2 N	AHz	31	IHz	414	lHz	Units
Characteristic	Symbol	Min	Max	Min	Max	Min	Max	
Cycle Time	TCYC	500		333		250		ns
Pulse Width, 02 Low	PW <sub>02L</sub>	210		160		100		ns
Pulse Width, 02 High	PW <sub>02H</sub>	220		170		110		ns
Clock Rise & Fall Time	T <sub>R</sub> , T <sub>F</sub>		15		12		10	ns
Pulse Width, 04 Low	PW <sub>04L</sub>	210		150		100		ns
Pulse Width, 04 High	PW <sub>04H</sub>	220		160		110		ns
Delay Time 02 to 04 Rise	Tavs	80	125		94 :		63	ns
Address Delay	TADS		100		75		50	ns
Address Hold Time (Address, R/W)	T <sub>HRW</sub>	20		20		20		ns
Address Valid to 04 Rise	T <sub>A04</sub>	25		18		12		ns
Data Delay Time (Write)	Торм		110		82		55	ns
Read Data Setup Time	T <sub>DSU</sub>	40		30		20		ns
Read Data Hold Time	THR	10		10		10		ns
Write Data Hold Time	T <sub>HW</sub>	30		30		30		ns
Read Access Time	TACC	340	-	254		168		ns
Processor Control Setup Time (RDY, S.O. Interrupts, Reset)	Taws	110		80	•	60		ns
Bus Enable Setup Time	TBE	125		100	,	75		ns

# D.C. CHARACTERISTICS

# Maximum Ratings

Rating	Symbol	Value	Unit
Supply Voltage	Vcc	-0.3 to +7.0	Vdc
Input Voltage	V <sub>in</sub>	-0.3 to +7.0	Vdc
Operating Temperature	т	1	°C
Commercial		0 to +70	-
Industrial		40 to +85	
Storage Temperature	T <sub>STG</sub>	-55 to +150	°C

## NOTE

This device contains input protection against damage to high static voltages or electric fields, however, precautions should be taken to avoid application of voltages higher than maximum rating.

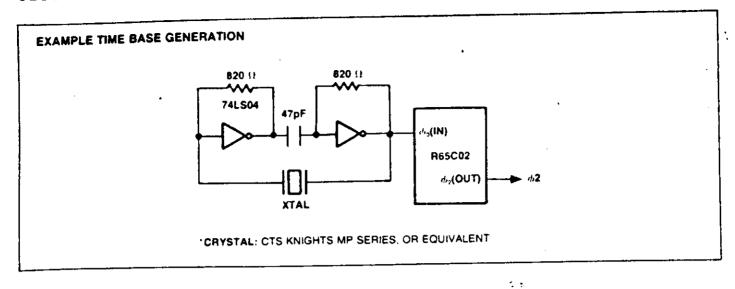
# **Electrical Characteristics**

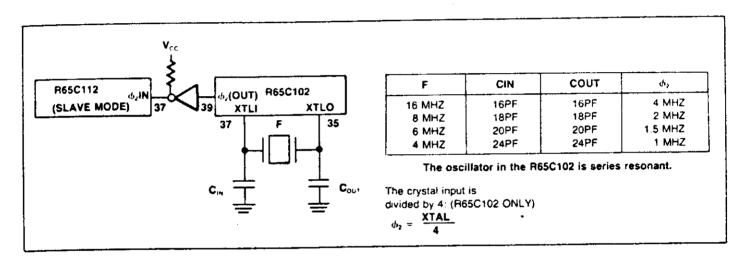
 $(V_{cc} = 5.0 \pm 20^{\circ}, V_{ss} = 0)$ 

Characteristic	Symbol	Min	Max	Unit
Input High Voltage All Input Pros (except φ₂ on R65C112)	V <sub>IH</sub>	2.0	V <sub>cc</sub> + 0.3	Vdc
Input Low Voltage 'Il Input Pins (except φ₂ on R65C112)	V <sub>n</sub>	-0.3	0.8	Vdc
Input High Voltage $\phi_{2, \text{in}}$ on R65C112	V <sub>IH</sub>	2.4	_	Vdc
Input Low Voltage φ <sub>2 in</sub> on R65C112	٧,,	_	0.4	Vdc
Input Leakage Current ( $V_{in}=0$ to 5.25V, $V_{cc}=0$ ) Logic (Excl. Rdy, S.O.) $\phi_{i}, \phi_{2}$ $\phi_{o(in)}$	I,n		1.0 1.0 1.0	μΑ
Three-State (Off State) Input Current (V <sub>in</sub> = 0.4 to 2.4V, V <sub>CC</sub> = 5.25V) Data Lines	I <sub>TS</sub> ,	_	10	Ащ
Output High Voltage ( $I_{LOAD} = -100 \mu Adc$ , $V_{cc} = 4.75V$ ) SYNC, Data, A0-A15, R/W, $\phi_1$ , $\phi_2$	V <sub>он</sub>	V <sub>ss</sub> + 2.4	_	Vdc
Output Low Voltage (I <sub>LOAD</sub> = 1.6 mAdc, V <sub>CC</sub> = 4.75V) SYNC, Data, A0-A15, R.W., φ <sub>1</sub> , φ <sub>2</sub>	Voi		V <sub>ss</sub> + 0.4	Vdc
Power Dissipation 0 MHz (Standby) 1 MHz 2 MHz 3 MHz 4 MHz Low Power (RDY = 0)	Po	_ _	10 20 40 60 80 10	μW mW
Capacitance at 25°C (V <sub>in</sub> = 0, f = 1 MHz	С			pF
Logic Data A0-A15, R/W, SYNC Φοίπ)	C <sub>out</sub> C <sub>out</sub> Cφ <sub>o(in)</sub>	_ _ _	5 10 10 10	
φ, φ₂	Cφ, Cφ,		30 50	

IRQ and NMI require external pull-up resistor.

# **CLOCK CONSIDERATIONS**

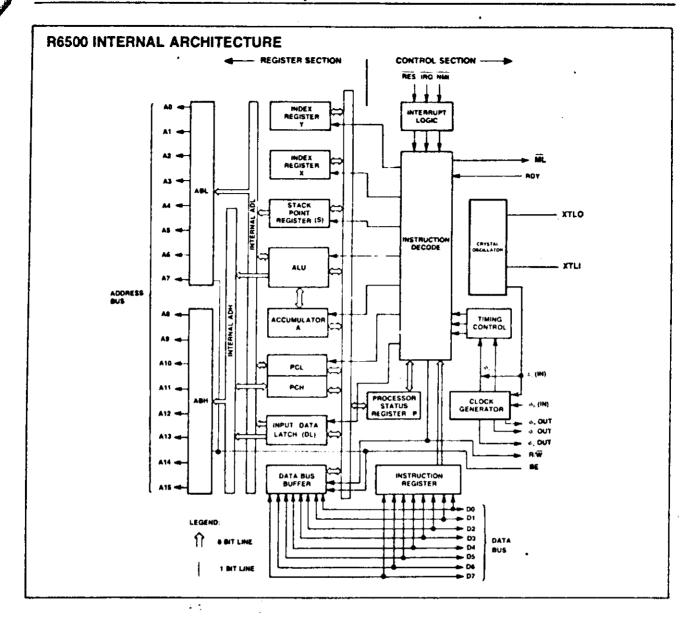




## NOMINAL CRYSTAL PARAMETERS

	3.58	4.0	6.0	8.0	16.0	MHZ
RS	60	50	30-50	20-40	10-30	Ω
CO	3.5	6.5	4-6	4-6	3-5	PF
C1	015	.025	.0102	.0102	.01+.02	PF
Q	740K	730K	720K	720K .	720K	K

Note: These represent at-cut crystal parameters only. Others may be used.



#### ELECTRONIC DEVICES DIVISION REGIONAL ROCKWELL SALES OFFICES

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Electronic Devices Division Rockwell International 4311 Jamboree Road Newport Beach, California 92660

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## UNITED STATES

Electronic Devices Division Rockwell International 1842 Reynolds Irvine, California 92714 (714) 833-4655 ESL 62108710 TWX 910 595-2518 Exectronic Devices Division Rockwell International 921 Bowser Road Richardson, Texas 75080 (214) 996-6500 Teiex 73 307

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#### FAR EAST

Electronic Devices Division
Rockwell International Overseas Corp
Hohpia Hirakawa-cho Bidg
7-5, 2-chorne Hirakawa-cho
Chiyoda-ku Tokyo 102 Japan
(03) 265-8806
Telex J22198

#### EUROPE

Electronic Devices Division Rockwell international GmbH Fraunholerstrasse 11 D-8033 Munchen-Martinsried West Germany (089) 857-6016 Telex 052/1/2650 rimd d

Electronic Devices Division Rockwell International Healthrow House Bath Rd Crantord Hourstow, Middlesex England (01) 759-9911 Teles 851-25463

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